

100V N-Channel Enhancement Mode MOSFET

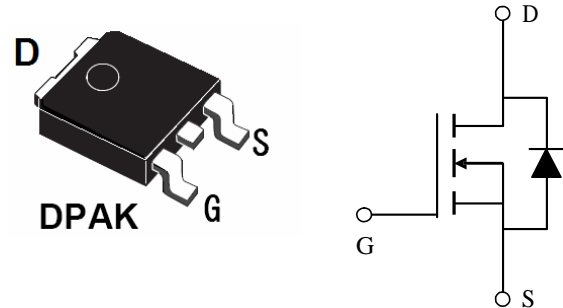
Description

The XPX100N10FD uses advanced technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 100V$ $I_D = 100A$

$R_{DS(ON)} < 5.9m\Omega @ V_{GS}=10V$



Application

Isolated DC

Motor control

Synchronous-rectification

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
XPX100N10FD	TO-252-3L	XPX100N10 XXX YYYY	2500

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current ¹	100	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current ¹	68	A
IDM	Pulsed Drain Current ²	210	A
EAS	Single Pulse Avalanche Energy ³	100	mJ
IAS	Avalanche Current	40	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	100	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	1.25	$^\circ C/W$

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Electrical Characteristics (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	108	---	V
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =13.5A	---	5.9	8.0	mΩ
	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =11.5A	---	8.7	10.5	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.8	2.3	V
IDSS	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =13.5A	---	75	---	S
Qg	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =13.5A	---	45	---	nC
Qg	Total Gate Charge (4.5V)		---	19.3	---	
Qgs	Gate-Source Charge		---	9.5	---	
Qgd	Gate-Drain Charge		---	4.8	---	
Td(on)	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3Ω, I _D =13.5A	---	10	---	ns
Tr	Rise Time		---	6.5	---	
Td(off)	Turn-Off Delay Time		---	45	---	
Tf	Fall Time		---	7.5	---	
Ciss	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	3313	---	pF
Coss	Output Capacitance		---	605	---	
Crss	Reverse Transfer Capacitance		---	20	---	
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	5	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.1	V
trr	Reverse Recovery Time	I _F =13.5A, di/dt=100A/μs, T _J =25°C	---	33	---	nS
Q _{rr}	Reverse Recovery Charge		---	150	---	nC

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、 The EAS data shows Max. rating . The test condition is V_{DD}=72V,V_{GS}=10V, L=0.1mH I_{AS}=40A
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation

Typical Characteristics

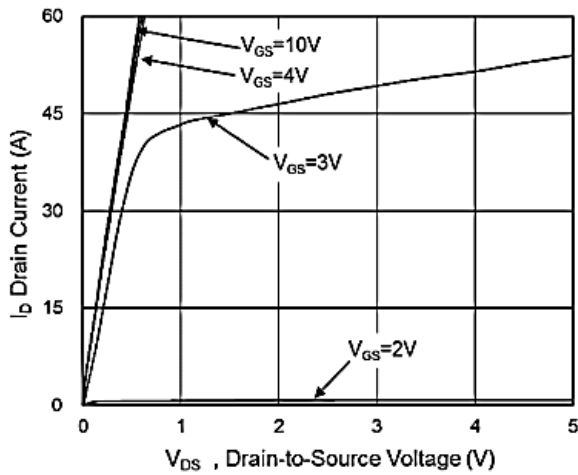


Fig.1 Typical Output Characteristics

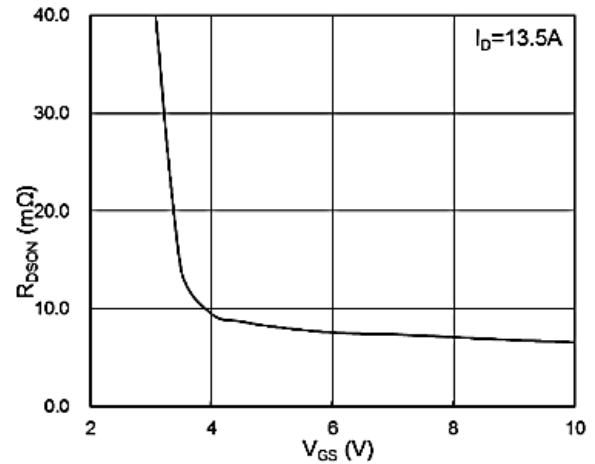


Fig.2 On-Resistance vs. G-S Voltage

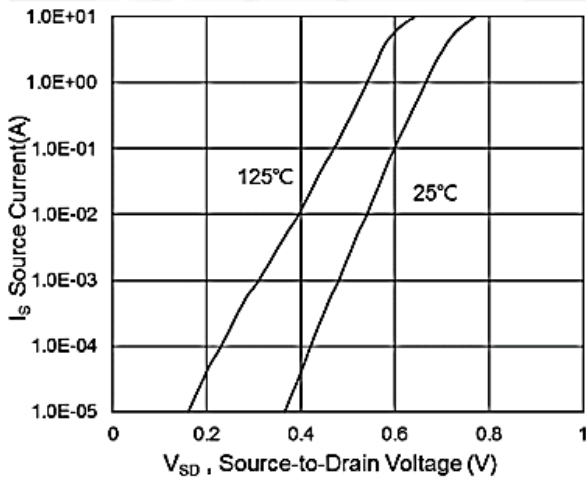


Fig.3 Source-Drain Forward Characteristics

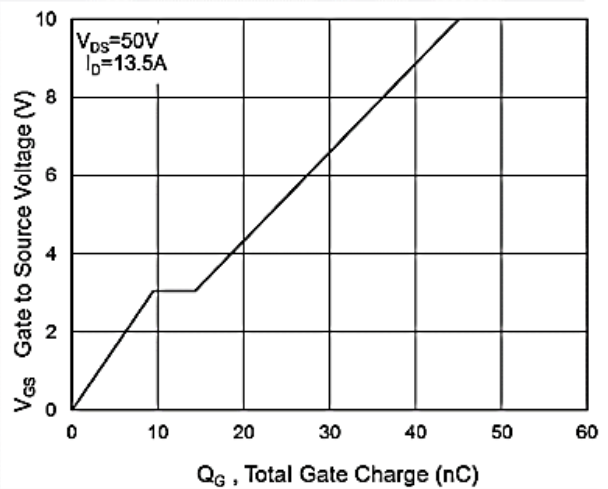


Fig.4 Gate-Charge Characteristics

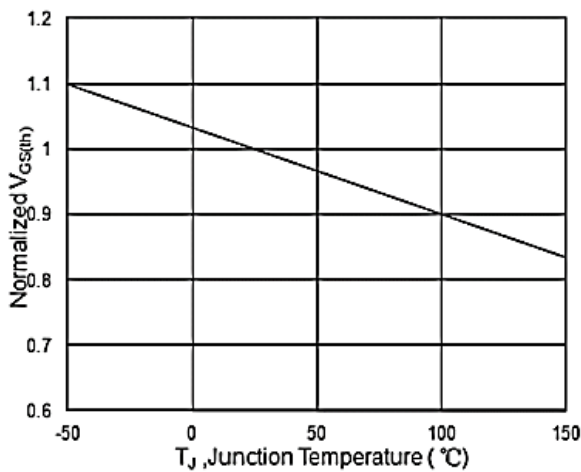


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

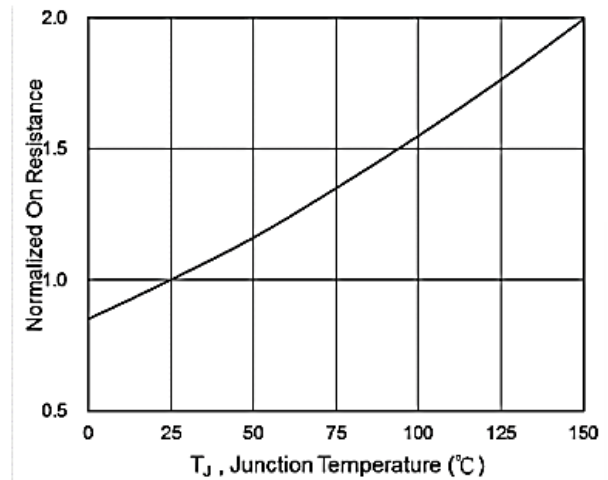


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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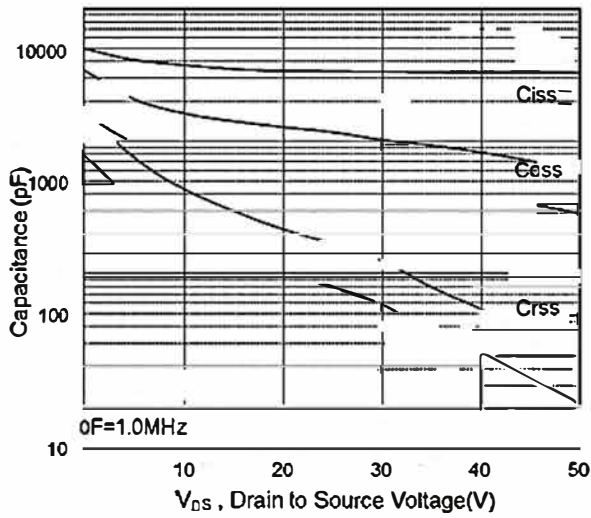


Fig.7 Capacitance

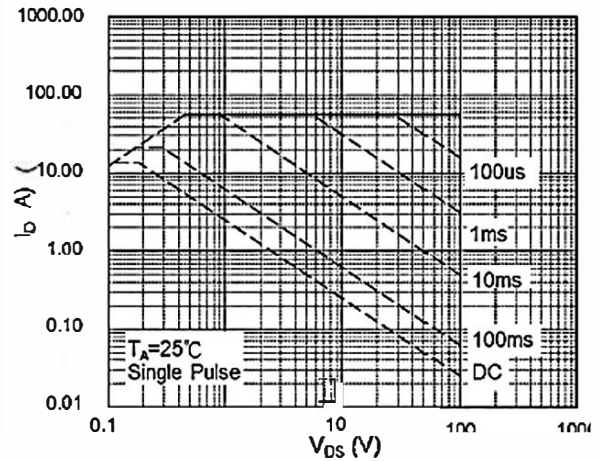


Fig.8 Safe Operating Area

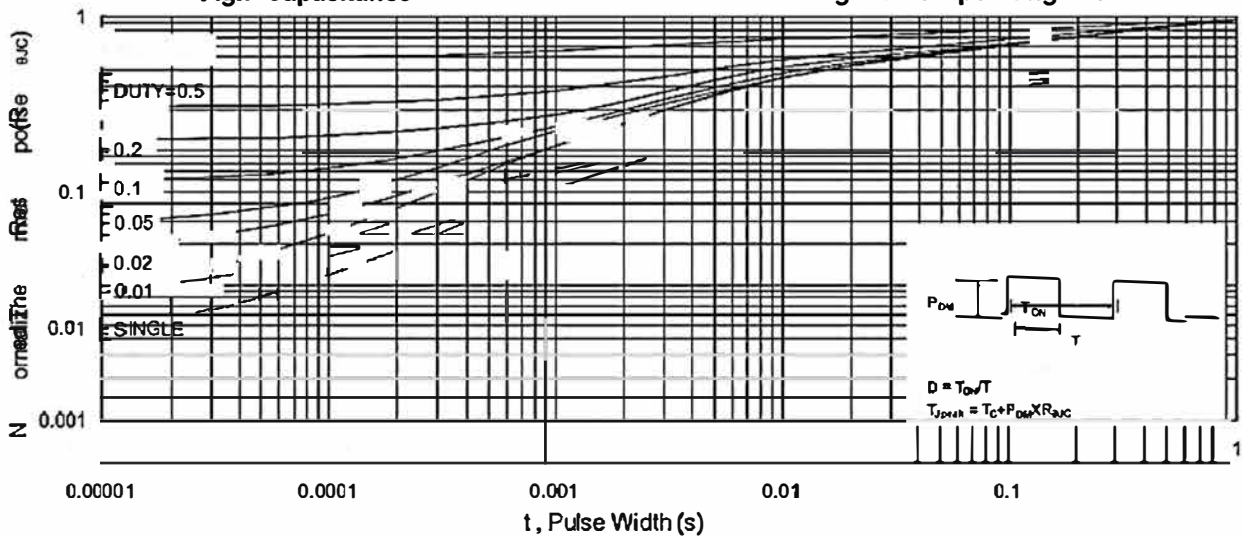


Fig.9 Normalized Maximum Transient Thermal Impedance

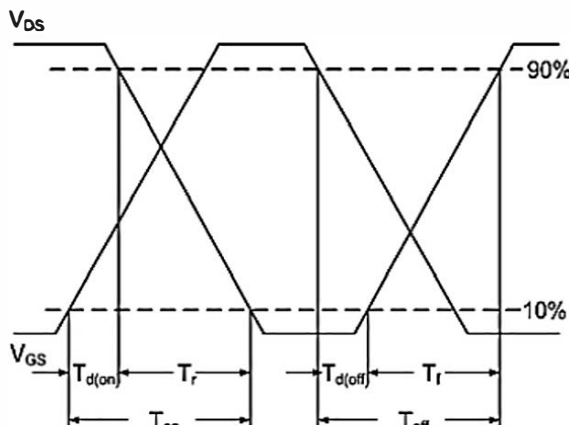


Fig.10 Switching Time Waveform

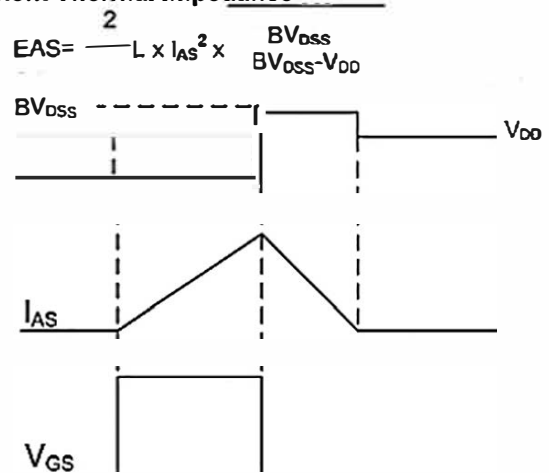
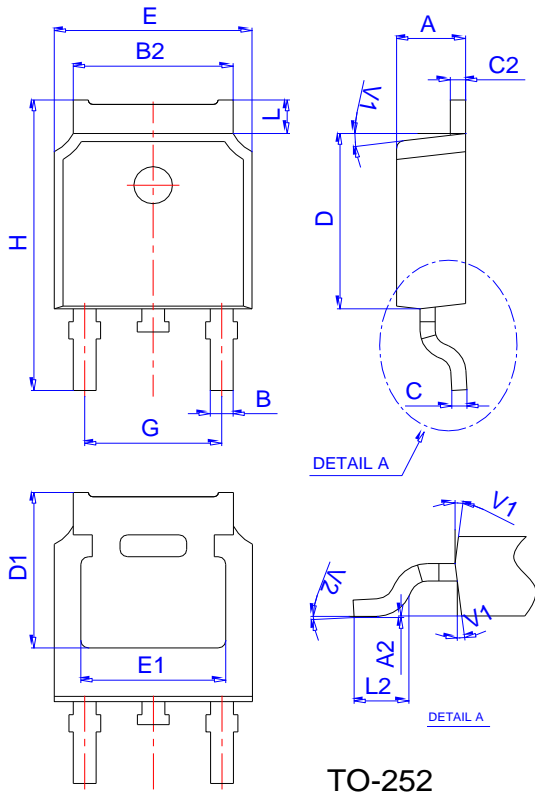


Fig.11 Unclamped Inductive Switching Waveform

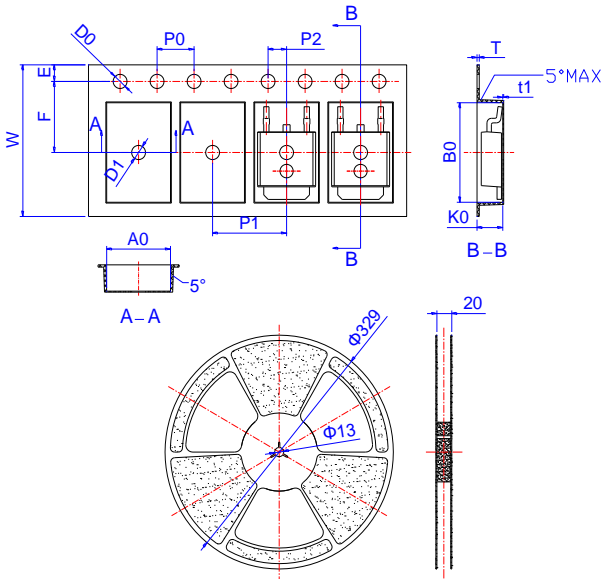
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Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1 sec
Pb-Free device	260°C +0/-5°C	5sec ±1 sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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